

Abstract

A method for non-destructively testing an IC device to determine the ESD performance.

A laser beam is used to probe the diffusions of the device. The amount of light absorbed by the  
5 diffusions is determined by monitoring the degree to which light is reflected by the device. The amount of reflection is related to the ESD susceptibility of the device in that the greater the amount of reflection, the worse the ESD performance of the device.

DEPARTMENT OF DEFENSE